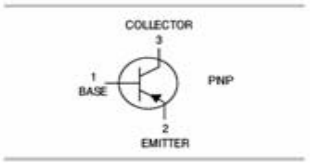
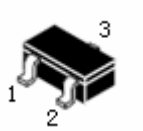
Silicon Epitaxial Planar Transistor **SS8550W**

FEATURES

Lead-free

- Collector Current.(I_C= 1.5A)
- Complementary To SS8550W.
- Collector Dissipation: P_C=0.2W (T_C=25°C)





SOT-323

APPLICATIONS

- High Collector Current.

ORDERING INFORMATION

Type No.	Marking	Package Code
SS8550W	Y2	SOT-323

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	**Parameter**	**Value**	**Units**
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1.5	A
P_C	Collector Dissipation	0.2	W
T_j,T_{stg}	Junction and Storage Temperature	-55~150	℃

Silicon Epitaxial Planar Transistor **SS8550W**

ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA,I_E=0	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-0.1mA,I_B=0	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-40V,I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=-20V,I_B=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-1V,I_C=-100mA	120		400	
		V_{CE}=-1V,I_C=-800mA	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-800mA, I_B= -80mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-800mA, I_B= -80mA			-1.2	V
Transition frequency	f_T	V_{CE}=-10V, I_C= -50mA f=30MHz	100			MHz
Output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz			20	pF
Base-emitter voltage	V_{BEF}	I_E=-1.5A			-1.6	V

CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H	J
Range	120-200	200-350	300-400

Silicon Epitaxial Planar Transistor **SS8550W**

TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

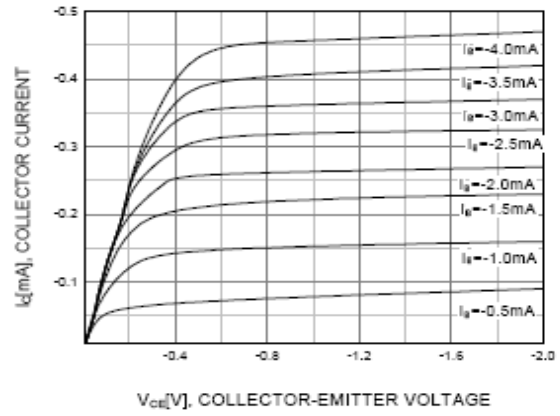


Figure 1. Static Characteristic

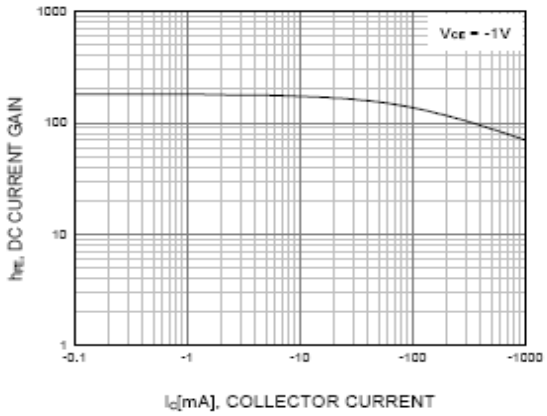


Figure 2. DC current Gain

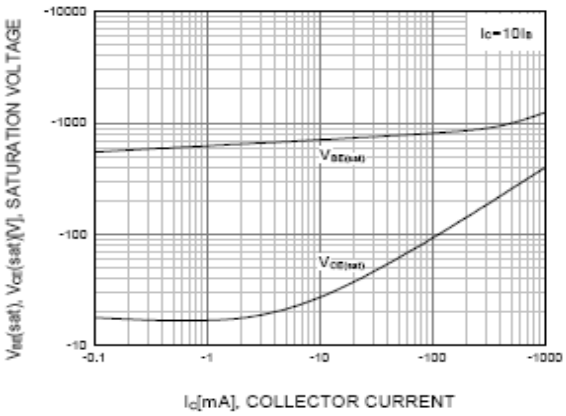


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

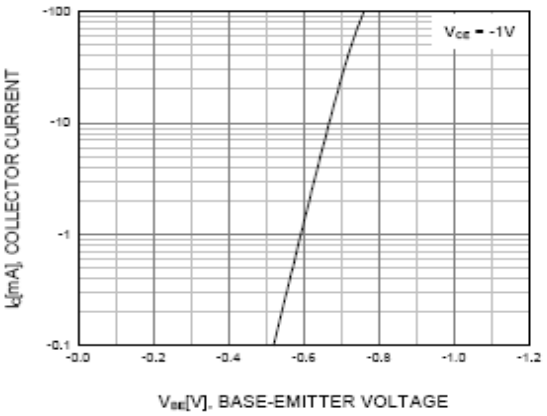


Figure 4. Base-Emitter On Voltage

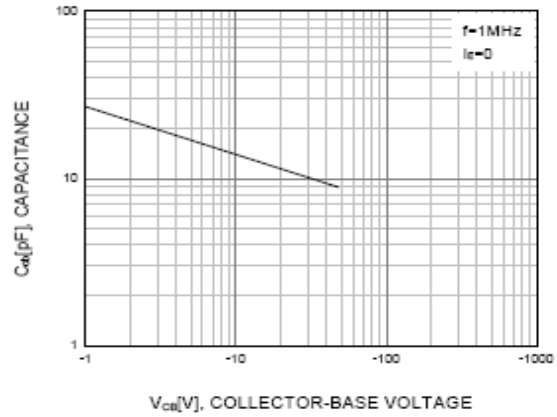


Figure 5. Collector Output Capacitance

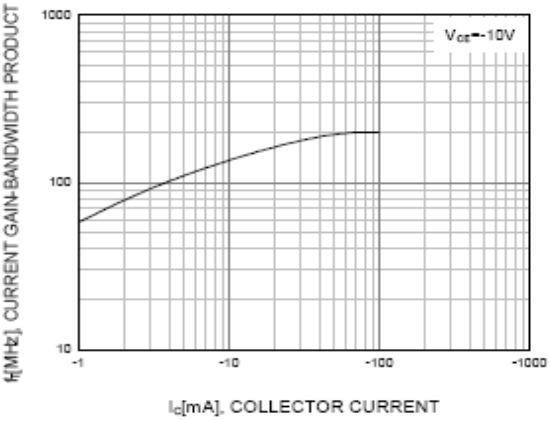
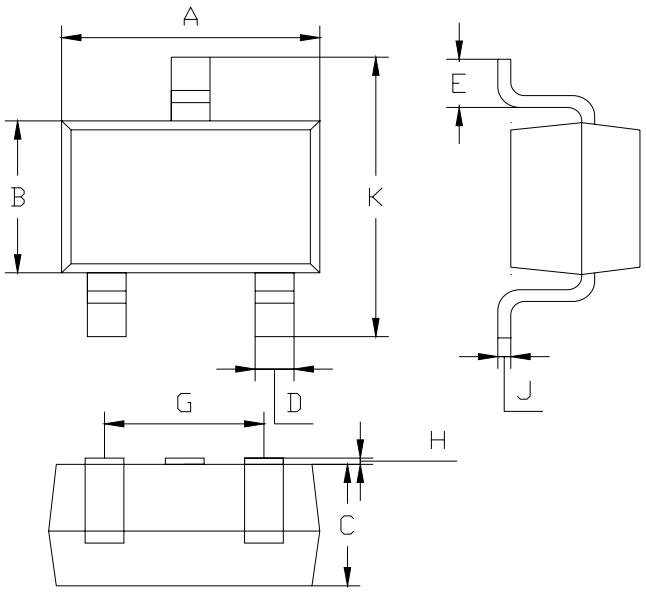


Figure 6. Current Gain Bandwidth Product

Silicon Epitaxial Planar Transistor **SS8550W**

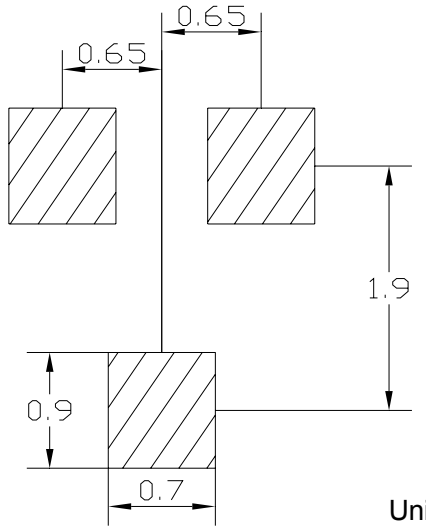
PACKAGE OUTLINE

Plastic surface mounted package SOT-323



SOT-323		
Dim	Min	Max
A	1.8	2.2
B	1.15	1.35
C	1.0Typical	
D	0.15	0.35
E	0.25	0.40
G	1.2	1.4
H	0.02	0.1
J	0.1Typical	
K	2.1	2.3
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
SS8550W	SOT-323	3000/Tape&Reel